Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The 74LVC244A is a high performance, non–inverting octal buffer operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows 74LVC244A inputs to be safely driven from 5 V devices. The 74LVC244A is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the output by placing them in a HIGH Z condition.

Features

- Designed for 1.2 V to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When V_{CC} = 0 V
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - ♦ Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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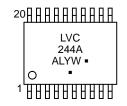


TSSOP-20 DT SUFFIX CASE 948E

QFN20 MN SUFFIX CASE 485AA

QFN20 MN SUFFIX CASE 485CB

MARKING DIAGRAMS







QFN20 - 485AA

QFN20 - 485CB

A = Assembly Location

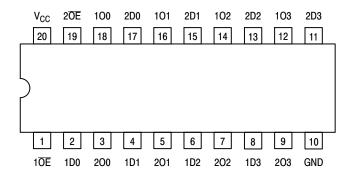
L = Wafer Lot Y = Year W = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.



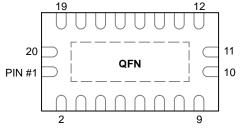


Figure 1. Pinout: 20-Lead (Top View)

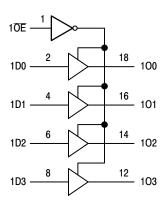
PIN NAMES

PINS	FUNCTION
nOE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3-State Outputs

TRUTH TABLE

INP	UTS	OUTPUTS
1 <u>0E</u> 2 <u>0E</u>	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

- H = High Voltage Level
- L = Low Voltage Level
- Z = High Impedance State
- X = High or Low Voltage Level and Transitions are Acceptable For I_{CC} reasons, DO NOT FLOAT Inputs



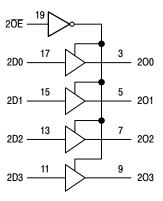


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
VI	DC Input Voltage		$-0.5 \le V_1 \le +6.5$	V
Vo	DC Output Voltage	Output in 3-State	$-0.5 \le V_O \le +6.5$	V
		Output in HIGH or LOW State (Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
I _{OK}	DC Output Diode Current	V _O < GND	-50	mA
		V _O > V _{CC}	+50	mA
Io	DC Output Source/Sink Current		±50	mA
Icc	DC Supply Current Per Supply Pin		±100	mA
I _{GND}	DC Ground Current Per Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds		T _L = 260	°C
TJ	Junction Temperature Under Bias		T _J = 135	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)		110.7	°C/W
MSL	Moisture Sensitivity	Level 1		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3-State	0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$			-24 -12	mA
I _{OL}	LOW Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$			24 12	mA
T _A	Operating Free–Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 1.65 V to 2.7 V V _{CC} = 2.7 V to 3.6 V	0		20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

^{1.} I_O absolute maximum rating must be observed.

^{2.} Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

DC ELECTRICAL CHARACTERISTICS

			-40°C to +85°C			-40°C to +125°C			
Symbol	Parameter	Conditions	Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	Unit
VIH	HIGH-level input	V _{CC} = 1.2 V	1.08	-	_	1.08	-	-	V
	voltage	V _{CC} = 1.65 V to 1.95 V	0.65 x V _{CC}	-	-	0.65 x V _{CC}	-	-	
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	-	
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	-	
V _{IL}	LOW-level input	V _{CC} = 1.2 V	-	_	0.12	-	_	0.12	V
	voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 x V _{CC}	_	-	0.35 x V _{CC}	
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	-	0.7	
		V _{CC} = 2.7 V to 3.6 V	_	_	0.8	-	_	0.8	
V _{OH}	HIGH-level output	$V_I = V_{IH} c$	or V _{IL}						V
	voltage	$I_O = -100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.2	-	-	V _{CC} - 0.3	-	-	
		$I_O = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	_	-	1.05	_	_	
		$I_O = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	-	
		$I_O = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	-	
		$I_O = -18 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	-	-	2.25	-	-	
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	-	
VOL	LOW-level output	$V_I = V_{IH}$ or V_{IL}					V		
	voltage	$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	-	-	0.2	_	-	0.3	
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	_	0.45	-	_	0.65	
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	ı	_	0.6	_	_	0.8	
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1	_	0.4	_	_	0.6	
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	1	_	0.55	_	_	0.8	
l _l	Input leakage current	$V_I = 5.5 V$ or GND $V_{CC} = 3.6 V$	1	±0.1	±5	_	±0.1	±20	μΑ
I _{OZ}	OFF-state output current	VI = VIH or VIL; $V_O = 5.5 \text{ V or GND}; V_{CC} = 3.6 \text{ V}$	-	±0.1	±5	_	±0.1	±20	μΑ
I _{OFF}	Power-off leakage current	$V_1 \text{ or } V_0 = 5.5 \text{ V}; V_{CC} = 0.0 \text{ V}$	ı	±0.1	±10	-	±0.1	±20	μΑ
I _{CC}	Supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6 \text{ V}$	1	0.1	10	_	0.1	40	μΑ
ΔI_{CC}	Additional supply current	per input pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.7 V to 3.6 V	_	5	500	-	5	5000	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. All typical values are measured at $T_A = 25^{\circ}C$ and $V_{CC} = 3.3$ V, unless stated otherwise.

AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}$)

			-40°C to +85°C -40°C to +125°C		25°C				
Symbol	Parameter	Conditions	Min	Typ ¹	Max	Min	Typ ¹	Max	Unit
t _{pd}	Propagation Delay (Note 5)	V _{CC} = 1.2 V	_	17.0	-	-	-	-	ns
	nDn to nOn	V _{CC} = 1.65 V to 1.95 V	1.5	6.4	13.7	1.5	-	15.8	
		V _{CC} = 2.3 V to 2.7 V	1.0	3.4	7.1	1.0	-	8.2	
		V _{CC} = 2.7 V	1.5	3.4	6.9	1.5	-	9.0	
		V _{CC} = 3.0 V to 3.6 V	1.5	2.9	5.9	1.5	-	7.5	
t _{en}	Enable Time (Note 6)	V _{CC} = 1.2 V	_	24.0	-	-	_	-	ns
	nOE to nOn	V _{CC} = 1.65 V to 1.95 V	1.5	7.0	17.3	1.5	-	20.0	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.5	3.9	9.5	1.5	-	11.0	
		V _{CC} = 2.7 V	1.5	4.1	8.6	1.5	-	11.0	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	3.2	7.6	1.0	-	9.5	
t _{dis}	Disable Time (Note 7)	V _{CC} = 1.2 V	_	9.0	-	-	-	-	ns
	nOE to nOn	V _{CC} = 1.65 V to 1.95 V	2.2	4.5	9.8	2.2	-	11.3	
		V _{CC} = 2.3 V to 2.7 V	0.5	3.6	5.5	0.5	-	6.4	
		V _{CC} = 2.7 V	1.5	3.3	6.8	1.5	-	8.5	
		V _{CC} = 3.0 V to 3.6 V	1.5	3.1	5.8	1.5	-	7.5	
t _{sk(0)}	Output Skew Time (Note 8)		_	-	1	-	_	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Typical values are measured at TA = 25°C and Vcc = 3.3 V, unless stated otherwise.
- 5. t_{pd} is the same as t_{PLH} and t_{PHL}.
- 6. ten is the same as tPZL and tPZH.
- 7. t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- 8. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 9)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 9)	$\begin{aligned} & V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ & V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

^{9.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit	
CIN	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	4	pF	
Соит	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	5	pF	
C_{PD}	Power Dissipation Capacitance	Per input; V _I = GND or V _{CC}			
	(Note 10)	V _{CC} = 1.65 V to 1.95 V	6.4		
		V_{CC} = 2.3 V to 2.7 V	9.6		
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	12.5		

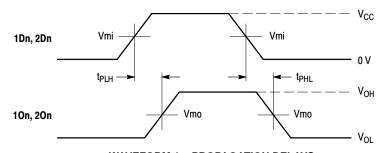
^{10.} C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times \text{fi x N} + \Sigma (C_L \times V_{CC}^2 \times \text{fo})$ where: fi = input frequency in MHz; fo = output frequency in MHz

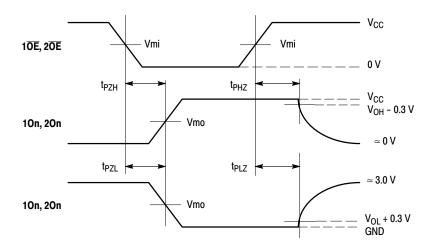
 C_L = output load capacitance in pF V_{CC} = supply voltage in Volts

N = number of outputs switching

 $[\]Sigma(C_L \times V_{CC}^2 \times fo) = \text{sum of the outputs.}$



 $\label{eq:waveform 1 - PROPAGATION DELAYS} t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

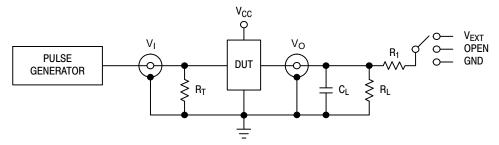


WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 3. AC Waveforms

	V _{CC}						
Symbol	3.3 V \pm 0.3 V	2.7 V	V _{CC} < 2.7 V				
Vmi	1.5 V	1.5 V	V _{CC} /2				
Vmo	1.5 V	1.5 V	V _{CC} /2				
V_{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V				
V_{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V				



 C_L includes jig and probe capacitance R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$ R_1 = R_L

Supply Voltage	Inp	out	Lo	ad	V _{EXT}		
V _{CC} (V)	V _I	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
1.65 – 1.95	V _{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V _{CC}	GND
2.3 – 2.7	V _{CC}	≤ 2 ns	30 pF	500 Ω	Open	2 x V _{CC}	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V _{CC}	GND
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V _{CC}	GND

Figure 4. Test Circuit

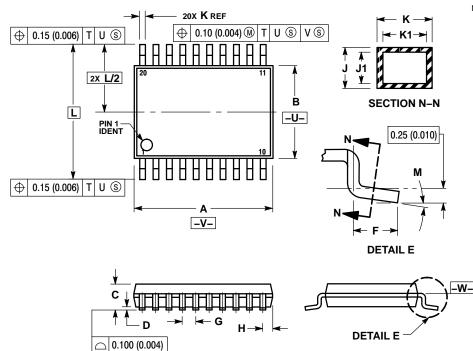
ORDERING INFORMATION

Device	Package	Shipping [†]
74LVC244ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
74LVC244AMN2TWG (In Development)	QFN20, 2.5x3.5 (Pb-Free)	3000 / Tape & Reel
74LVC244AMNTWG (In Development)	QFN20, 2.5x4.5 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 **ISSUE C**



-T- SEATING PLANE

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE

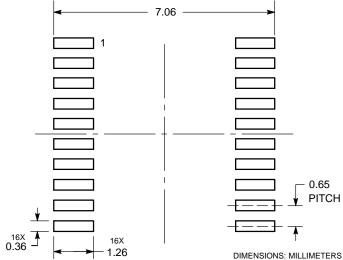
 - 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
 - CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W.—.

DETERMINED AT DATOWIFEAINE -VV									
	MILLIN	IETERS	INC	HES					
DIM	MIN	MAX	MIN	MAX					
Α	6.40	6.60	0.252	0.260					
В	4.30	4.50	0.169	0.177					
C		1.20		0.047					
D	0.05	0.15	0.002	0.006					
F	0.50	0.75	0.020	0.030					
G	0.65	BSC	0.026 BSC						
Н	0.27	0.37	0.011	0.015					
J	0.09	0.20	0.004	0.008					
J1	0.09	0.16	0.004	0.006					
K	0.19	0.30	0.007	0.012					
K1	0.19	0.25	0.007	0.010					
L	6.40 BSC		0.252 BSC						
M	0°	8°	0°	8°					

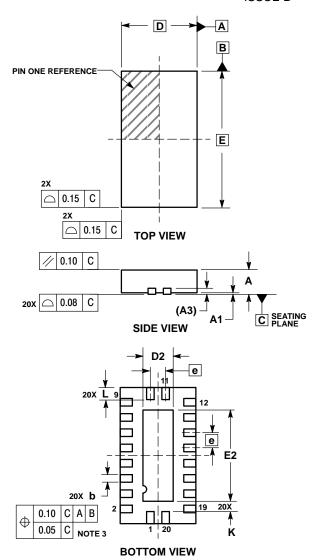
SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

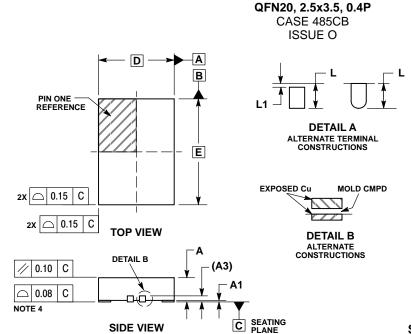
QFN20, 2.5x4.5 MM CASE 485AA ISSUE B



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.50 BSC	
D2	0.85	1.15
E	4.50 BSC	
E2	2.85	3.15
е	0.50 BSC	
K	0.20	
1	0.35	0.45

PACKAGE DIMENSIONS



0.10 C A B

 Φ

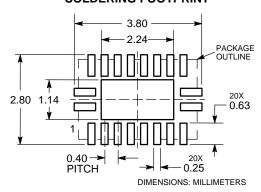
0.10 C A B

NOTES:

- DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS & APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN
 1.15 AND 0.30 MM FROM TERMINAL TIP.
 COPLANARITY APPLIES TO THE EXPOSED
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.15	0.25
D	2.50 BSC	
D2	0.90	1.10
Е	3.50 BSC	
E2	2.00	2.20
е	0.40 BSC	
L	0.35	0.45
L1		0.15

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

E2

20x b

0.10 C A B

0.05 C NOTE 3

E/2

BOTTOM VIEW

 \oplus

D2

20X L

DETAIL A

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